

### Abstract of the Disclosure

- A semiconductor device having a thin film formed by atomic layer deposition and a method for fabricating the same, wherein the semiconductor device includes a liner layer formed on an internal wall and bottom of a trench, gate spacers formed on the
- 5 sidewalls of gate stack patterns functioning as a gate line, a first bubble prevention layer formed on the gate spacers and the gate stack patterns, bit line spacers formed on the sidewalls of bit line stack patterns functioning as a bit line, and a second bubble prevention layer formed on the bit line spacers and the gate stack patterns and at least
- 10 one of the above is formed of a multi-layer of a silicon nitride layer and a silicon oxide layer, or a multi-layer of a silicon oxide layer and a silicon nitride layer, thereby filling the trench, gate stack patterns, or bit line stack patterns without a void.